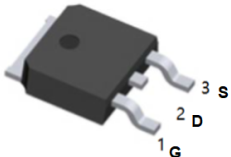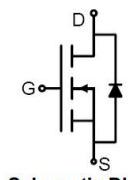# UMW®

60V N-Channel Enhancement Mode Power MOSFET

General Description

The STD30NF06 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

Features

● V_{DS} = 60V,ID =30A

　$R_{DS(ON)}$,23m Ω (Typ) @ VGS =10V

　$R_{DS(ON)}$,29m Ω (Typ) @ VGS =4.5V

● Advanced Trench Technology

● Excellent $R_{DS(ON)}$ and Low Gate Charge

● Lead free product is acquired

Application

● Load Switch

● PWM Application

● Power management

TO-252(DPAK) top view

Schematic Diagram

Absolute Maximum Ratings(TA=25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous[Note3]	TC=25℃	I_D	30	A
	TC=100℃		20	A
Drain Current-Pulsed[Note1]		I_{DM}	120	A
Avalanche Energy[Note4]		E_{AS}	72	mJ
Maximum Power Dissipation	TC=25℃	P_D	55	W
Storage Temperature Range		T_{STG}	-55 to +150	℃
Operating Junction Temperature Range		T_J	-55 to +150	℃

Thermal Resistance

Parameter	Symbol	Min.	Typ.	Max	Unit
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	-	-	2.7	℃/W

Electrical Characteristics(TJ=25℃ unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_{DS}=250uA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	VGS(TH)	V_{DS}=V_{GS},I_{DS}=250uA	1.0	1.6	2.5	V
Drain-Source On-State Resistance	RDS(ON)	V_{GS}=10V,I_{DS}=15A	-	23	29	mΩ
		V_{GS}=4.5V,I_{DS}=10A	-	29	40	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C_{iSS}	VDS =25V, VGS = 0V, f=1MHz	-	1562	-	pF
Output Capacitance	C_{OSS}		-	75.4	-	
Reverse Transfer Capacitance	C_{rss}		-	66.8	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$	V_{GS}=10V,V_{Ds}=30V, R_{GEN}=1.8Ω I_D=15A	-	7.5	-	ns
Rise Time	t_r		-	21	-	
Turn-Off Delay Time	$T_{d(off)}$		-	16	-	
Fall Time	t_f		-	23.5	-	
Total Gate Charge at 10V	Q_g	V_{DS}=30V,I_{DS}=15A, V_{GS}=10V	-	25	-	nC
Gate to Source Gate Charge	Q_{gs}		-	4.5	-	
Gate to Drain"Miller"Charge	Q_{gd}		-	6.5	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_{DS}=15A	-	-	1.2	V
Reverse Recovery Time	t_{rr}	TJ=25℃,IF=15A di/dt=100A/us	-	29	-	nS
Reverse Recovery Charge	Q_{rr}		-	45	-	nC

Notes:

1: Repetitive rating, pulse width limited by maximum junction temperature.

2: Surface mounted on FR4 Board, t≤10sec.

3: Pulse width ≤ 300μs, duty cycle ≤ 2%.

4: EAS condition: L=0.5mH,VDD=30V,VG=10V,VGATE=60V,Start TJ=25℃.

Typical Performance Characteristics
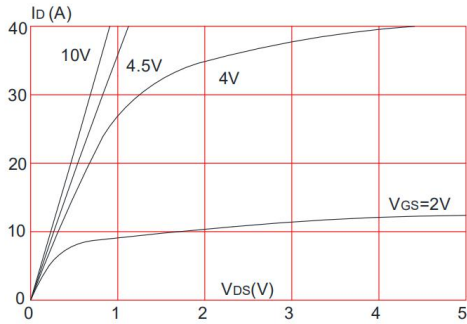
Figure1: Output Characteristics

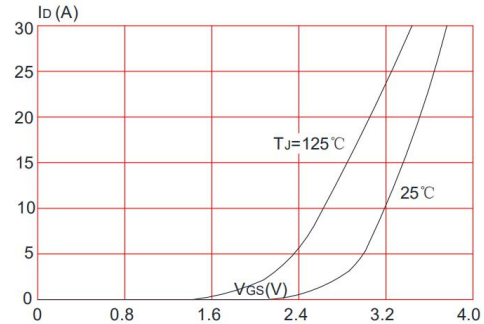**Figure 2:** Typical Transfer Characteristics

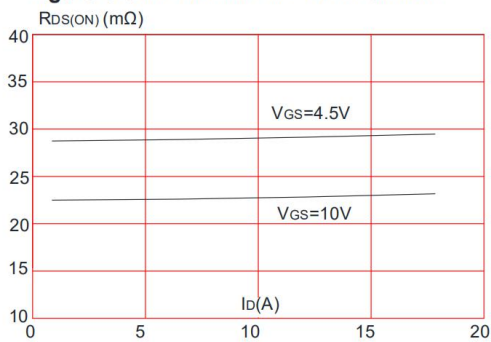
Figure 3: On-resistance vs. Drain Current
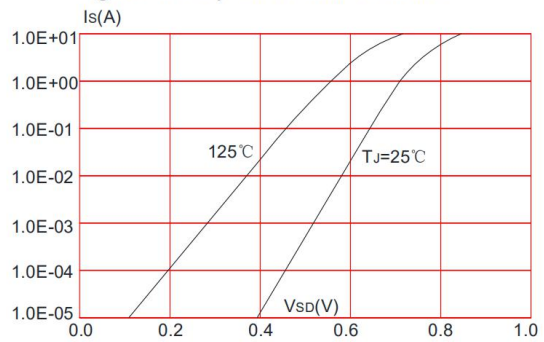

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

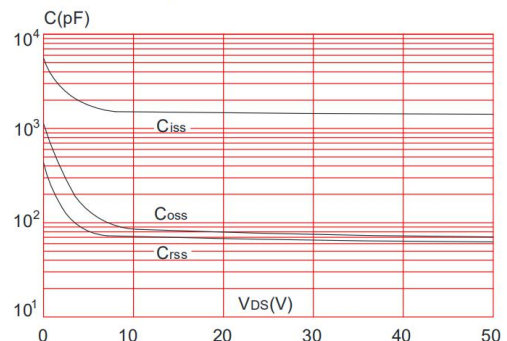**Figure 6:** Capacitance Characteristics

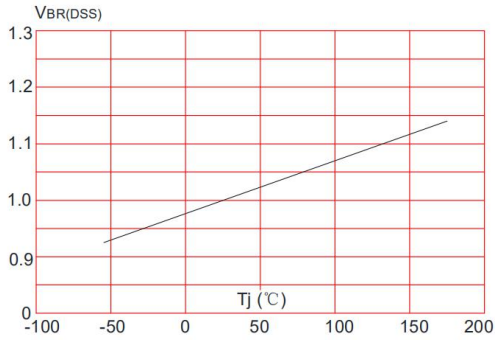**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

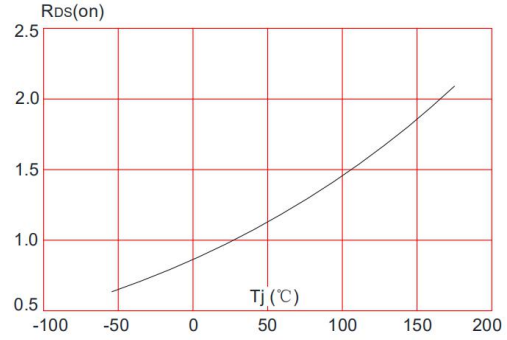**Figure 8:** Normalized on Resistance vs. Junction Temperature
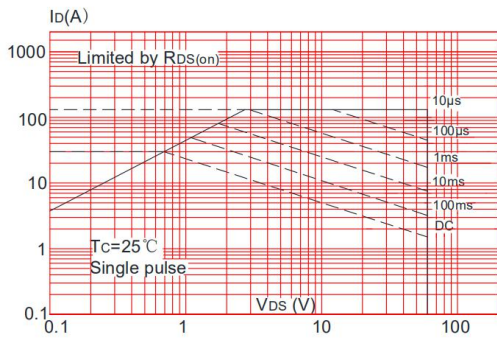

Figure 9: Maximum Safe Operating Area

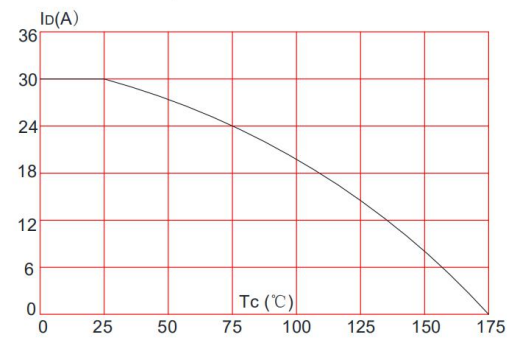**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

Notes:
1. Duty factor $D=t_1/t_2$
2. Peak $T_J = P_{DM} \cdot Z_{thJC} + T_C$

Test Circuit

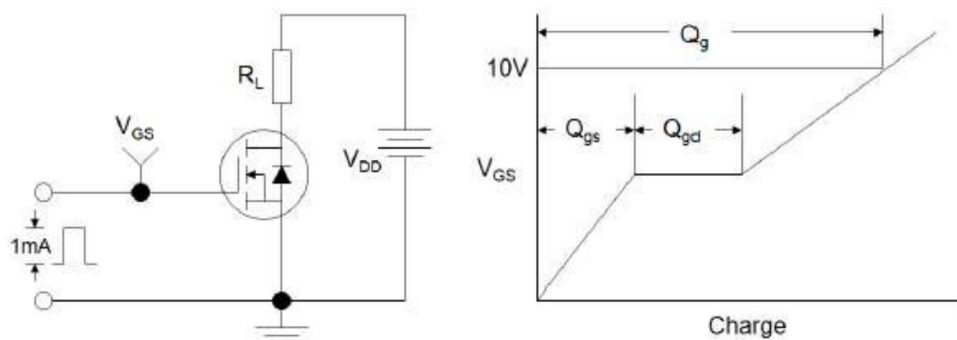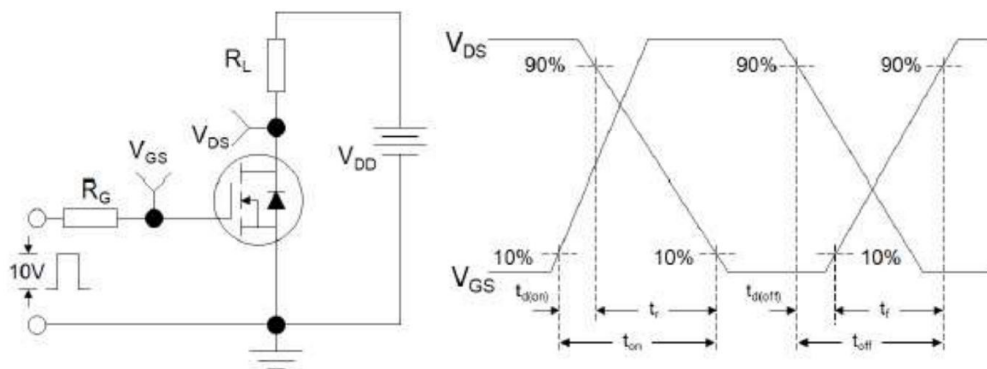Figure1:Gate Charge Test Circuit & Waveform
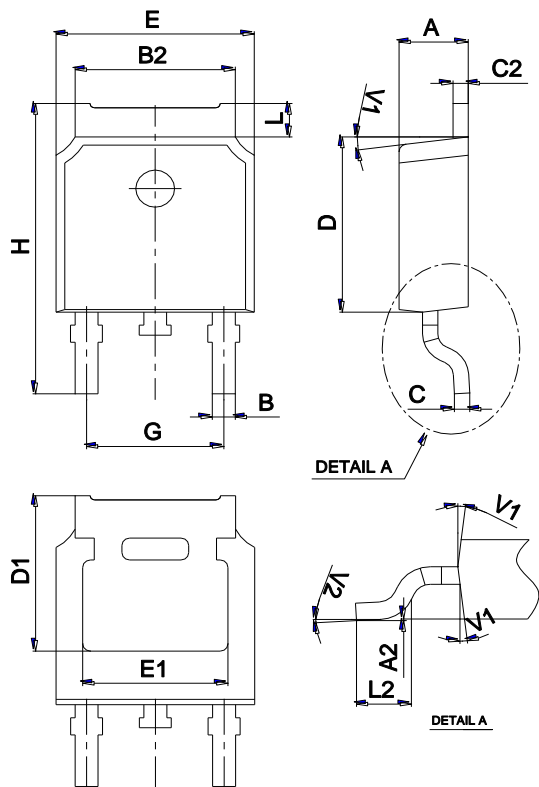

Figure 2: Resistive Switching Test Circuit & Waveforms

Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

60V N-Channel Enhancement Mode Power MOSFET

Package Mechanical Data TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Ordering information

Order code	Package	Baseqty	Delivery mode
UMW STD30NF06L	TO-252	2500	Tape and reel

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